DRA9114T

Silicon PNP epitaxial planar type

For digital circuits Complementary to DRC9114T DRA5114T in SSMini3 type package

Features

- \bullet High forward current transfer ratio h_{FE} with excellent linearity
- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

Packaging

Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

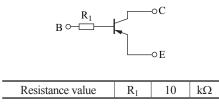
Absolute Maximum Ratings $T_a = 25^{\circ}C$ Parameter Unit Symbol Rating Collector-base voltage (Emitter open) -50 V V_{CBO} Collector-emitter voltage (Base open) -50V V_{CEO} Collector current -100 $I_{\rm C}$ mA mW Total power dissipation \mathbf{P}_{T} 125 150 °C Junction temperature T_i Storage temperature -55 to +150 °C T_{stg}

Package

- Code
- SSMini3-F3-B
- Pin Name
 - 1: Base
 - 2: Emitter
 - 3: Collector

Marking Symbol: LD

Internal Connection



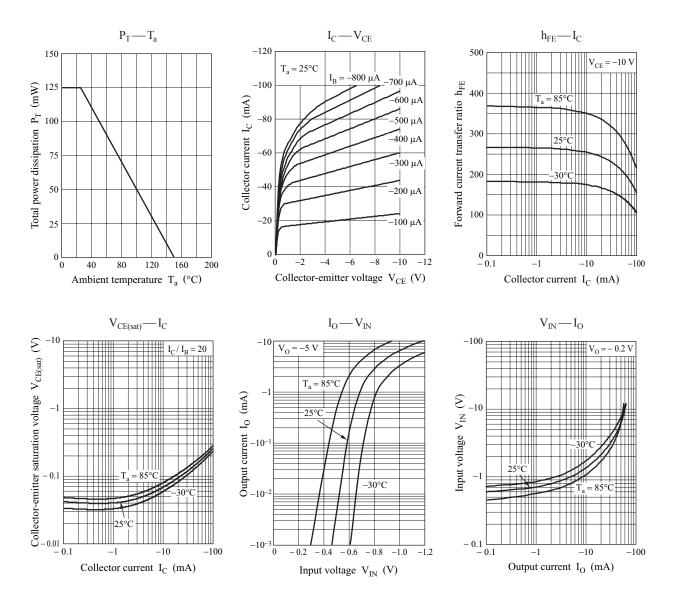
Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \ \mu {\rm A}, I_{\rm E} = 0$	-50			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 {\rm mA}, I_{\rm B} = 0$	-50			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = -50 \text{ V}, I_E = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{\rm CE} = -50 \text{ V}, I_{\rm B} = 0$			-0.5	μΑ
Emitter-base cutoff current (Collector open)	I _{EBO}	$V_{EB} = -6 \text{ V}, I_C = 0$			-0.01	mA
Forward current transfer ratio	h _{FE}	$V_{\rm CE} = -10$ V, $I_{\rm C} = -5$ mA	160		460	
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -0.5 \text{ mA}$			-0.25	V
Input voltage (ON)	V _{I(on)}	$V_{CE} = -0.2 \text{ V}, I_C = -5 \text{ mA}$	-1.2			V
Input voltage (OFF)	V _{I(off)}	$V_{CE} = -5 \text{ V}, I_C = -100 \mu\text{A}$			-0.4	V
Input resistance	R ₁		-30%	10	+30%	kΩ

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

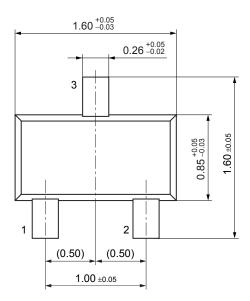
DRA9114T

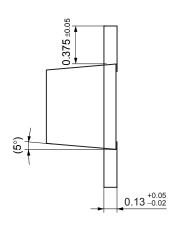
Panasonic

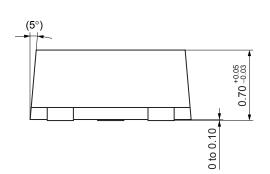


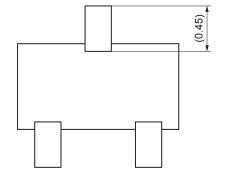
SSMini3-F3-B

Unit: mm









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